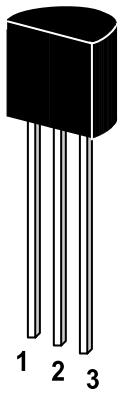
ST 2SC2362

NPN Silicon Epitaxial Planar Transistor
High -Voltage Low-Noise Amp applications

The transistor is subdivided into three groups F, G and H, according to its DC current gain.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	120	V
Collector Emitter Voltage	V_{CEO}	100	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Collector Current (Pulse)	I_{CP}	100	mA
Collector Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	125	^{O}C
Storage Temperature Range	T_S	-55 to +125	^{O}C

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Characteristics at T_{amb}=25 ^{O}C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=6V, I_C=1mA					
Current Gain Group F	h_{FE}	160	-	320	-
G	h_{FE}	280	-	560	-
H	h_{FE}	480	-	960	-
Collector Base Breakdown Voltage					
at I_C=10μA	$V_{(BR)CBO}$	120	-	-	V
Collector Emitter Breakdown Voltage					
at I_C=1mA	$V_{(BR)CEO}$	100	-	-	V
Emitter Base Breakdown Voltage					
at I_E=10μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
atV_{CB}=80V	I_{CBO}	-	-	1	μA
Emitter Cutoff Current					
atV_{EB}=4V	I_{EBO}	-	-	1	μA
Collector Emitter Saturation Voltage					
at I_C=10mA, I_B=1mA	$V_{CE(sat)}$	-	-	0.5	V
Gain Bandwidth Product					
at V_{CE}=6V, I_C=1mA	f_T	-	130	-	MHz
Output Capacitance					
at V_{CB}=10V, f=1MHz	C_{OB}	-	1.8	-	pF
Noise Level					
at V_{CC}=30V, I_C=1mA					
R_g=56KΩ,V_G=77dB/1kHz	$C_{NO(ave)}$	-	-	35	mV
Noise Peak Level					
at V_{CC}=30V, I_C=1mA					
R_g=56KΩ,V_G=77dB/1kHz	$C_{NO(peak)}$	-	-	200	mV